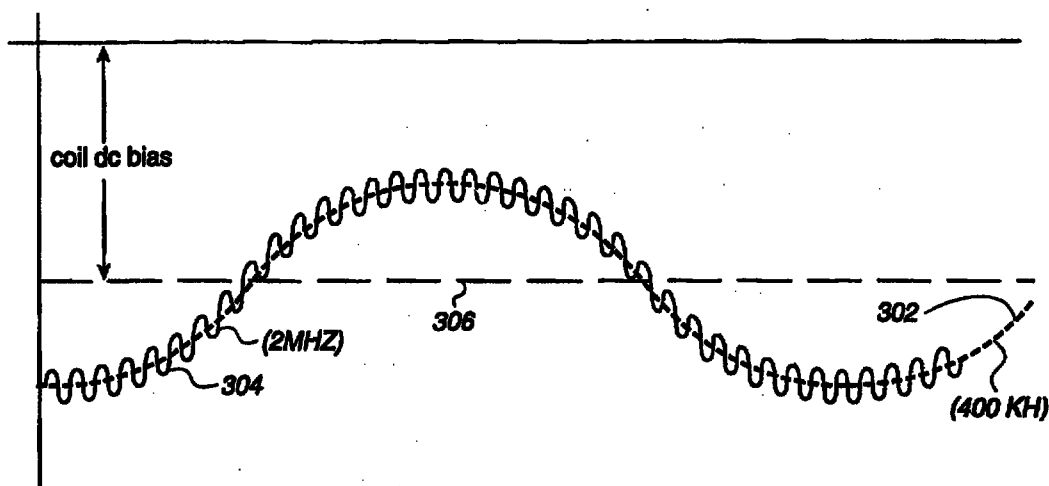




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(54) Title: MODULATED POWER FOR IONIZED METAL PLASMA DEPOSITION



(57) Abstract

In a plasma deposition system for depositing a film of sputtered target material on a substrate, the output of an RF generator coupled to a coil for generating a plasma can be varied during the deposition process so that heating and sputtering of the RF coil can be more uniform by "time-averaging" RF voltage distributions along the RF coil. In another embodiment, RF energy applied to a coil positioned to sputter material onto a workpiece, is modulated to control the biasing of the coil. As a consequence, control of coil sputtering may be improved such that the uniformity of deposition may also be improved.